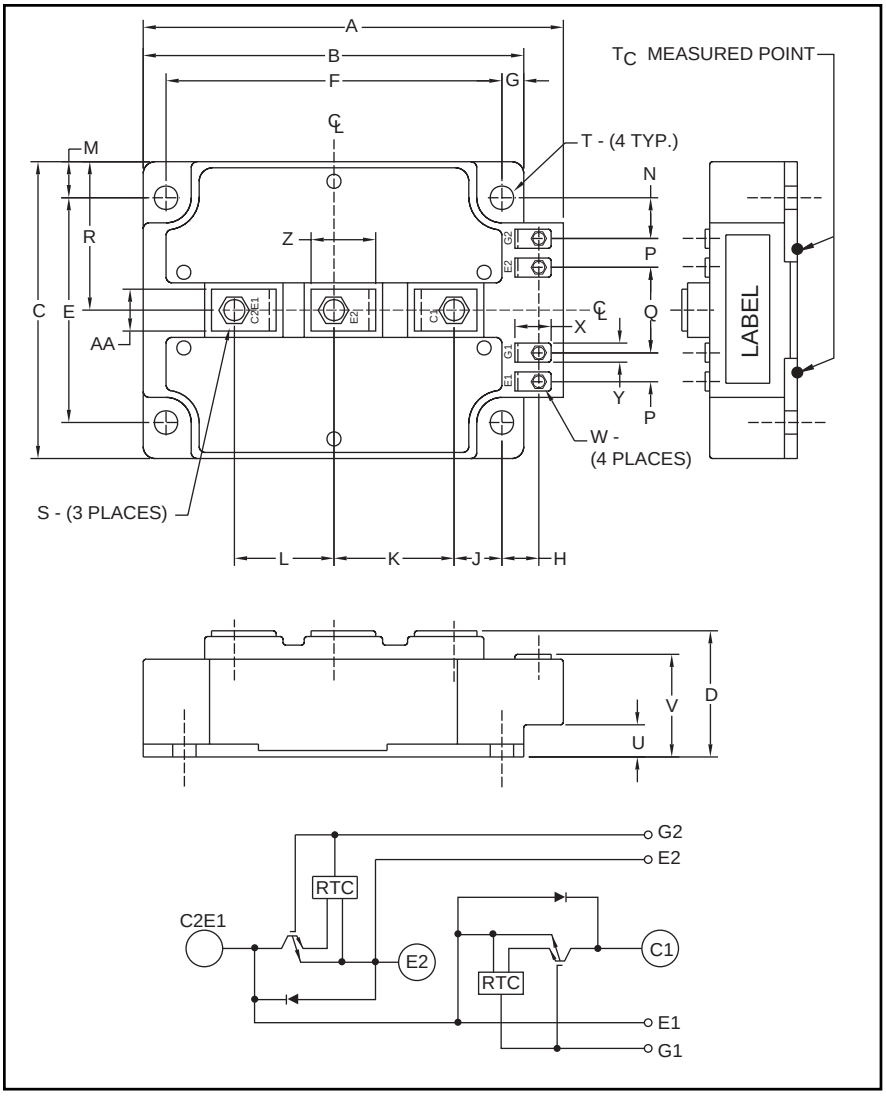
Powerex, Inc., 200 E. Hillis Street, Youngwood, Pennsylvania 15697-1800 (724) 925-7272

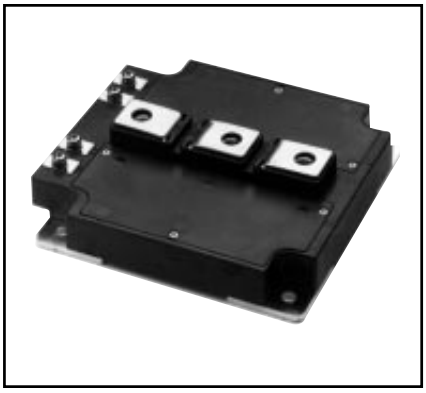
Dual IGBTMOD™ F-Series Module
400 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	5.51	140.0
B	5.12	130.0
C	5.12	130.0
D	1.38 +0/-0.02	35.0 +0/-0.5
E	4.33±0.01	110.0±0.25
F	4.33±0.01	110.0±0.25
G	0.39	10.0
H	0.45	11.5
J	0.54	13.8
K	1.72	43.8
L	1.42	36.0
M	0.39	10.0
N	0.80	20.4

Dimensions	Inches	Millimeters
P	0.57	14.5
Q	1.57	40.0
R	2.56	65.0
S	M8	M8
T	0.32	8.0
U	0.32	8.0
V	0.97 +0.04/-0.02	24.5 +1.0/-0.5
W	M4	M4
X	0.59	15.0
Y	0.35	9.0
Z	1.02	26.0
AA	0.79	20.0



Description:
Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:
- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:
- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies
- ☐ Laser Power Supplies

Ordering Information:
Example: Select the complete module number you desire from the table - i.e. CM400DU-24F is a 1200V (V_{CES}), 400 Ampere Dual IGBTMOD™ Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	400	24

Absolute Maximum Ratings, T_j = 25 °C unless otherwise specified

Ratings	Symbol	CM400DU-24F	Units
Junction Temperature	T_j	-40 to 150	°C
Storage Temperature	T_{stg}	-40 to 125	°C
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	±20	Volts
Collector Current (T_C = 25°C)	I_C	400	Amperes
Peak Collector Current	I_{CM}	800*	Amperes
Emitter Current** (T_C = 25°C)	I_E	400	Amperes
Peak Emitter Current**	I_{EM}	800*	Amperes
Maximum Collector Dissipation (T_C = 25°C, $T_j \leq$ 150°C)	P_C	1100	Watts
Mounting Torque, M8 Main Terminal	–	95	in-lb
Mounting Torque, M6 Mounting	–	40	in-lb
G(E) Terminal, M4	–	15	in-lb
Weight	–	1200	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	Volts

Static Electrical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}$, V_{GE} = 0V	–	–	2	mA
Gate Leakage Voltage	I_{GES}	$V_{GE} = V_{CES}$, V_{CE} = 0V	–	–	80	µA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	I_C = 40mA, V_{CE} = 10V	5.0	6	7.0	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 400A, V_{GE} = 15V, T_j = 25°C	–	1.8	2.4	Volts
		I_C = 400A, V_{GE} = 15V, T_j = 125°C	–	1.9	–	Volts
Total Gate Charge	Q_G	V_{CC} = 600V, I_C = 400A, V_{GE} = 15V	–	4400	–	nC
Emitter-Collector Voltage**	V_{EC}	I_E = 400A, V_{GE} = 0V	–	–	3.2	Volts

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.
**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Dynamic Electrical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance		C_{ies}	V_{CE} = 10V, V_{GE} = 0V	–	–	160	nf
Output Capacitance		C_{oes}		–	–	6.8	nf
Reverse Transfer Capacitance		C_{res}		–	–	4	nf
Resistive	Turn-on Delay Time	$t_{d(on)}$	V_{CC} = 600V, I_C = 400A,	–	–	450	ns
Load	Rise Time	t_r	V_{GE1} = V_{GE2} = 15V,	–	–	200	ns
Switch	Turn-off Delay Time	$t_{d(off)}$	R_G = 3.1Ω,	–	–	1000	ns
Times	Fall Time	t_f	Inductive Load	–	–	300	ns
Diode Reverse Recovery Time*		t_{rr}	Switching Operation	–	–	550	ns
Diode Reverse Recovery Charge*		Q_{rr}	I_E = 400A	–	23.6	–	µC

Thermal and Mechanical Characteristics, T_j = 25 °C unless otherwise specified

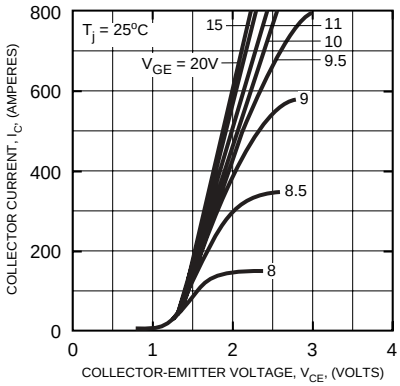
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}Q$	Per IGBT 1/2 Module, T_c Reference Point per Outline Drawing	–	–	0.11	°C/W
Thermal Resistance, Junction to Case	$R_{th(j-c)}R$	Per FWDi 1/2 Module, T_c Reference Point per Outline Drawing	–	–	0.13	°C/W
Thermal Resistance	$R_{th(j-c')}Q$	Per IGBT 1/2 Module T_c Reference Point Under Chips	–	–	0.045**	°C/W
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	–	0.010	–	°C/W

*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

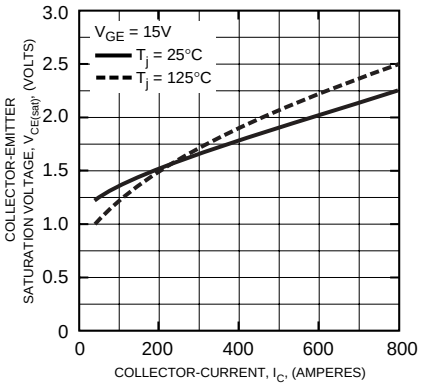
**If you use this value, $R_{th(f-a)}$ should be measured just under the chips.

CM400DU-24F
Dual IGBTMOD™ F-Series Module
400 Amperes/1200 Volts

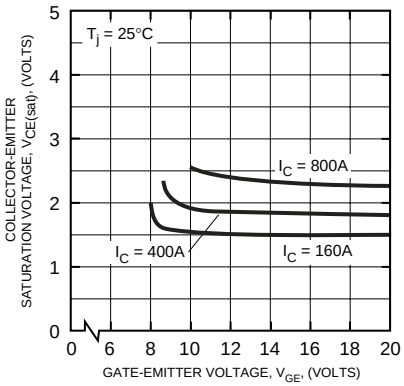
OUTPUT CHARACTERISTICS (TYPICAL)



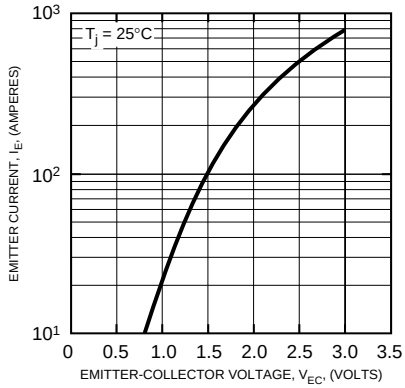
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



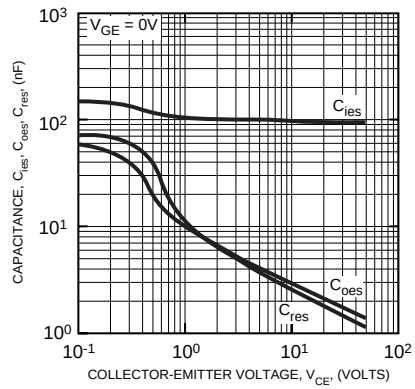
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



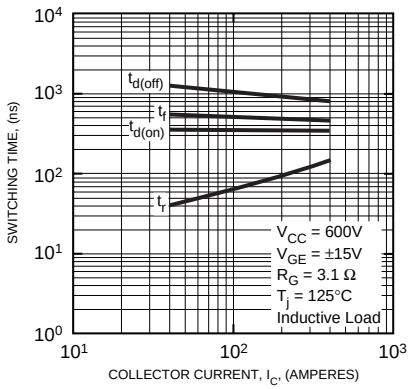
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



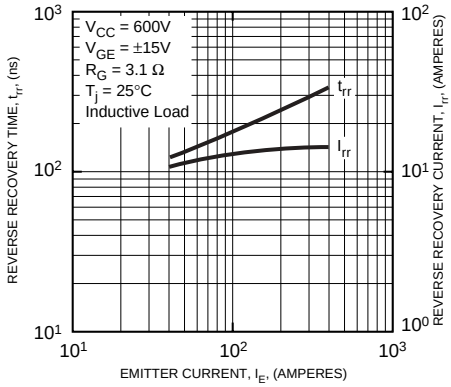
CAPACITANCE VS. V_{CE} (TYPICAL)



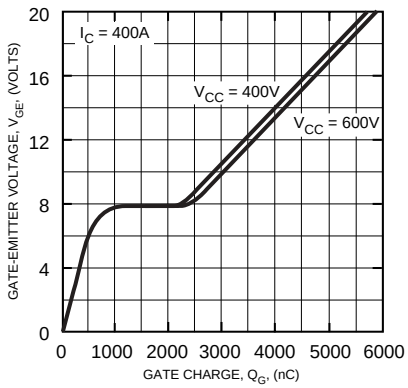
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



GATE CHARGE, V_{GE}



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT & FWDi)

